

United States Patent [19]

Hama et al.

[54] PLASMA PROCESS APPARATUS

[75] Inventors: Kiiichi Hama, Chino; Jiro Hata;
Toshiaki Hongoh, both of
Yamanashi-ken, all of Japan

[73] Assignee: Tokyo Electron Limited, Tokyo, Japan

[*] Notice: The term of this patent shall not extend
beyond the expiration date of Pat. No.
5,525,159.

[21] Appl. No.: 624,102

[22] Filed: Mar. 29, 1996

Related U.S. Application Data

[63] Continuation of Ser. No. 357,423, Dec. 16, 1994, Pat. No.
5,525,159.

[30] Foreign Application Priority Data

Dec. 17, 1993	[JP]	Japan	5-343871
Mar. 23, 1994	[JP]	Japan	6-076717
Mar. 23, 1994	[JP]	Japan	6-076727

[51] Int. Cl.⁶ C23C 16/00

[52] U.S. Cl. 118/723 I; 118/723 R;
156/345

[58] Field of Search 118/723 R, 723 MP,
118/723 MW, 723 MA, 723 E, 723 I, 723 IR,
719, 723 AN, 723 ER; 156/345; 204/298.01,
298.02, 298.31, 298.25, 298.26, 298.35

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009070-0262460

[11] Patent Number: 5,792,261

[45] Date of Patent: *Aug. 11, 1998

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Primary Examiner—R. Bruce Breneman

Assistant Examiner—Luz Alejandro

Attorney, Agent, or Firm—Obion, Spivak, McClelland,
Maier & Neustadt, P.C.

[57] ABSTRACT

A plasma CVD apparatus for forming a silicon film on an LCD substrate includes a container which is divided into process and upper chambers by a quartz partition plate. A work table on which the substrate is mounted is arranged in the process chamber and a lower electrode to which a high frequency potential is applied is arranged in the work table. First lower and second upper supply heads are arranged between the partition plate and the work table in the process chamber. SiH_4 and H_2 gas and He gases are supplied through the first and second supply heads. He gas is transformed into plasma while SiH_4 and H_2 gas is excited and decomposed by the plasma thus formed. Two coils are arranged in the upper chamber and high frequency voltages are applied to the coils to generate electromagnetic field to induce the transforming of He gas into plasma. High frequency voltages applied to the coils are the same in phase and directions of current flowing through adjacent portions of the coils are the same.

16 Claims, 10 Drawing Sheets

009070 "028460